## Electronic Supplementary Information for

## Non-Destructive Characterization of Extended Crystalline Defects in Confined Semiconductor Device Structures

authored by

Andreas Schulze,<sup>1,\*</sup> Libor Strakos,<sup>2</sup> Tomas Vystavel,<sup>2</sup> Roger Loo,<sup>1</sup> Antoine Pacco,<sup>1</sup> Nadine Collaert,<sup>1</sup> Wilfried Vandervorst,<sup>1,3</sup> and Matty Caymax<sup>1</sup>

<sup>1</sup>Imec, Kapeldreef 75, 3001 Leuven, Belgium

<sup>2</sup>Thermo Fisher Scientific, Mat. & Struct. Analysis (formerly FEI), Vlastimila Pecha 12, 62700 Brno, Czech Republic

<sup>3</sup>KU Leuven, Department of Physics and Astronomy, Celestijnenlaan 200D, 3001 Leuven, Belgium

\* Corresponding author: <u>Andreas.Schulze@imec.be</u>

## **Table of contents**

p S1: Cover sheet

p S2: Experimental details (sample fabrication)

## **Experimental details (sample fabrication)**

A schematic representation illustrating the fabrication of the SiGe fins by selective epitaxy into trenches is shown in figure S1.



**Figure S1.** Schematic representation illustrating the selective epitaxial growth of the SiGe fin structures studied in this paper. Fins of different width are grown simultaneously on the same substrate under identical growth conditions.

More details regarding the fabrication process can be found in:

R. Loo et al., Processing Technologies for Advanced Ge Devices. ECS Journal of Solid State Science and Technology. 6(1), 2017.